High Speed Current Mode PWM Control IC for Switching Power Supply

HITACHI

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Description

The HA17384S/H and HA17385H are PWM control switching regulator IC series suitable for highspeed, current-mode switching power supplies. With ICs from this series and a few external parts, a small, low cost flyback-transformer switching power supply can be constructed, which facilitates good line regulation by current mode control. Synchronous operation driven after an external signal can also be easily obtained which offers various applications such as a power supply for monitors small multi-output power supply.

The IC series are composed of circuits required for a switching regulator IC. That is a under-voltage lockout (UVL), a high precision reference voltage regulator (5.0 V \pm 2%), a triangular wave oscillator for timing generation, a high-gain error amplifier, and as totem pole output driver circuit which directly drives the gate of power MOSFETs found in main switching devices. In addition, a pulse-by-pulse type, high-speed, current-detection comparator circuit with variable detection level is incorporated which is required for current mode control.

The HA17384SPS includes the above basic function circuits. In addition to these basic functions, the H Series incorporates thermal shut-down protection (TSD) and overvoltage protection (OVP) functions, for configuration of switching power supplies that meet the demand for high safety levels.

Between the HA17384 and HA17385, only the UVL threshold voltages differ as shown in the product lineup table. (See next page.)

This IC is pin compatible with the "3842 family" ICs made by other companies in the electronics industry. However, due to the characteristics of linear ICs, it is not possible to achieve ICs that offer full compatibility in every detail.

Therefore, when using one of these ICs to replace another manufacturer's IC, it must be recognized that it has different electrical characteristics, and it is necessary to confirm that there is no problem with the power supply (mounting) set used.



Functions

- Under-voltage lockout system
- Reference voltage regulator of 5.0 V \pm 2%
- Triangular wave (sawtooth) oscillator
- Error amplifier
- Totem pole output driver circuit (direct driving for power MOSFETs)
- Current-detection comparator circuit for current mode
- OVP function (over voltage protection) *1
- TSD function (thermal shut-down protection) *1
- Protect function by zener diode (between power input and GND)

Note: 1. H series only.

Features

- High-safety UVL circuit is used (Both V_{IN} and Vref are monitored)
- High speed operation:
 - Current detection response time: 100 ns Typ
 - Maximum oscillation frequency: 500 kHz
- Low standby current: 170 μA Typ
- Wide range dead band time
 - (Discharge current of timing capacitance is constant 8.4 mA Typ)
- Able to drive power MOSFET directly
 - (Absolute maximum rating of output current is ± 1 A peak)
- OVP function (over voltage protection) is included *1
 - (Output stops when FB terminal voltage is 7.0 V Typ or higher)
- TSD function (thermal shut-down protection) is included *1
 - (Output stops when the temperature is 160°C Typ or higher)
- · Zener protection is included
 - (Clamp voltage between V_{IN} and GND is 34 V Typ)
- Wide operating temperature range:
 - Operating temperature: -20°C to +105°C
 - Junction temperature: 150°C *2

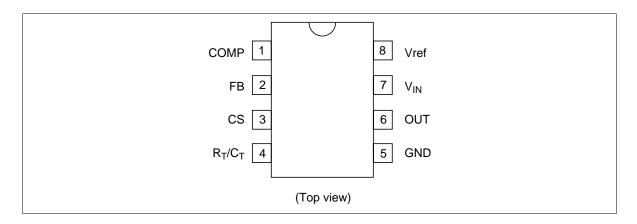
Note: 1. H series only.

2. S series only.

Product Line-up

Package		Additional Functio	n	UVL Power Sup Threshold Volt	• •
DILP8 (DP-8)	SOP8 (FP-8DC)	TSD (Thermal shut- down protection)	OVP (Over voltage protection)	V _{TH UVL} (V) Typ	V _{TL UVL} (V) Typ
HA17384SPS	HA17384SRP	_	_	16.0	10.0
HA17384HPS	HA17384HRP	0	0	_	
HA17385HPS	HA17385HRP	0	О	8.4	7.6

Pin Arrangement

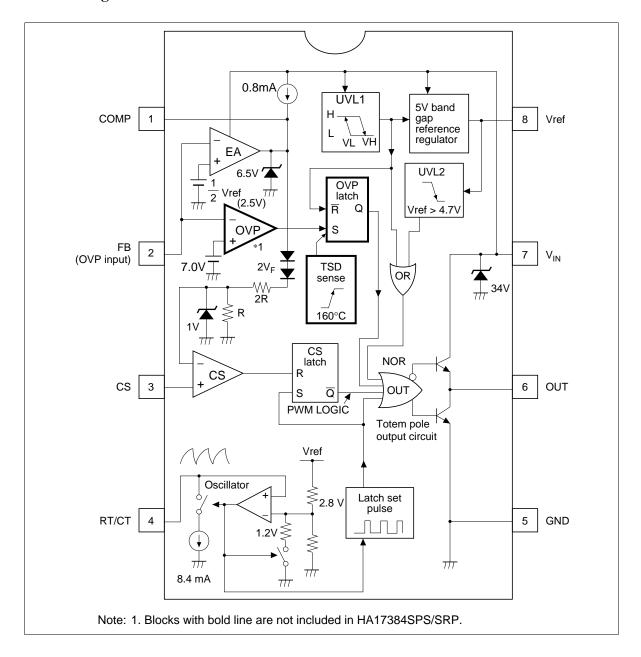


Pin Function

Pin No.	Symbol	Function	Note
1	COMP	Error amplifier output pin	
2	FB	Inverting input of error amp./OVP input pin	1
3	CS	Current sensing signal input pin	
4	R _T /C _T	Timing resistance, timing capacitance connect pin	
5	GND	Groung pin	
6	OUT	PWM Pulse output pin	
7	V _{IN}	Power supply voltage input pin	
8	Vref	Reference voltage 5V output pin	

Note: 1. Overvoltage protection (OVP) input is usable only for the HA17384H and HA17385H.

Block Diagram



Absolute Maximum Ratings

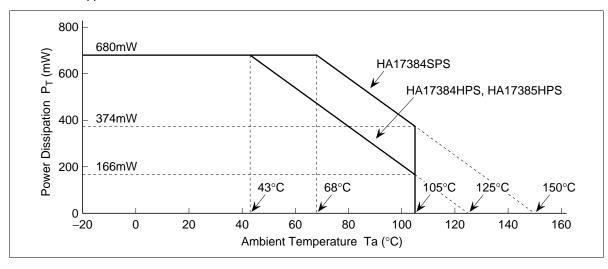
Item	Symbol	Rating	Unit	Note
Supply voltage	V _{IN}	30	V	
DC output current	Io	±0.1	Α	
Peak output current	I _{O PEAK}	±1.0	Α	
Error amplifier input voltage	$V_{\sf FB}$	–0.3 to V _{IN}	V	
COMP terminal input voltage	V _{COMP}	-0.3 to +7.5	V	
Error output sink current	I _{OEA}	10	mA	
Power dissipation	P _T	680	mW	1, 2
Operating temperature	Topr	-20 to +105	°C	
Junction temperature	Tj	125	°C	3
		150	°C	4
Storage temperature	Tstg	-55 to +125	°C	3
		-55 to +150	°C	4

Notes: 1. For the HA17384HPS and HA17385HPS,

This value applies up to $Ta = 43^{\circ}C$; at temperatures above this, 8.3 mW/°C derating should be applied.

For the HA17384SPS,

This value applies up to $Ta = 68^{\circ}C$; at temperatures above this, 8.3 mW/°C derating should be applied.



Absolute Maximum Ratings (cont)

Notes: 2. This is the value when the device is mounted on a glass-epoxy substrate (40 mm \times 40 mm \times 1.6 mm). However,

For the HA17384HRP and HA17385HRP,

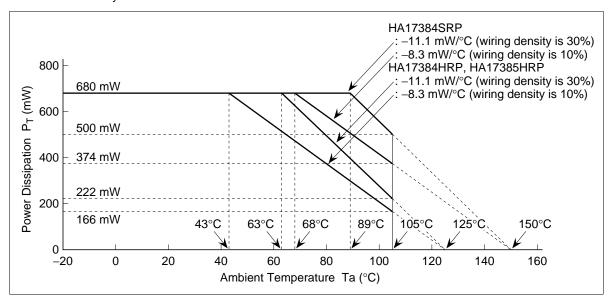
Derating should be performed with 8.3 mW/°C in the Ta \geq 43°C range if the substrate wiring density is 10%.

Derating should be performed with 11.1 mW/°C in the $Ta \ge 63$ °C range if the substrate wiring density is 30%.

For the HA17384SRP,

Derating should be performed with 8.3 mW/ $^{\circ}$ C in the Ta \geq 68 $^{\circ}$ C range if the substrate wiring density is 10%.

Derating should be performed with 11.1 mW/°C in the Ta \geq 89°C range if the substrate wiring density is 10%.



- 3. Applies to the HA17384HPS/HRP and HA17385HPS/HRP.
- 4. Applies to the HA17384SPS/SRP.

Electrical Characteristics

(The condition is: Ta = 25°C, $V_{IN} = 15$ V, $C_{T} = 3300$ pF, $R_{T} = 10$ k Ω without notice)

Reference Part

Item	Symbol	Min	Тур	Max	Unit	Test Condition	Note
Reference output voltage	Vref	4.9	5.0	5.1	V	lo = 1 mA	
Line regulation	Regline		20	50	mV	12 V ≤ V _{IN} ≤ 25 V	
Load regulation	Regload	_	10	25	mV	-1 mA ≥ lo ≥ -20 mA	
Output short current	los	-30	-100	-180	mA	Vref = 0V	
Temperature stability	ΔVref	_	80	_	ppm/°C	Io = −1 mA, −20°C ≤ Ta ≤ 105°C	1
Output noise voltage	V _N		100	_	μV	10 Hz ≤ fnoise ≤ 10 kHz	1

Notes: 1. Reference value for design.

Triangular Wave Oscillator Part

Item	Symbol	Min	Тур	Max	Unit	Test Condition	Note
Typical oscillating frequency	fosc Typ	47	52	57	kHz	$C_T = 3300 \text{ pF},$ $R_T = 10 \text{ k}\Omega$	
Maximum oscillating frequency	fosc Max	500	_	_	kHz		
Supply voltage dependency of oscillating frequency	∆fosc 1	_	±0.5	±2.0	%	$12~\text{V} \leq \text{V}_{\text{IN}} \leq 25~\text{V}$	
Temperature dependency of oscillating frequency	∆fosc 2	_	±5.0	_	%	–20°C ≤ Ta ≤ 105°C	1
Discharge current of C _⊤	Isink _{CT}	7.5	8.4	9.3	mΑ	V _{CT} = 2.0 V	
Low level threshold voltage	V _{TLCT}	_	1.2	_	V		1
High level threshold voltage	V_{THCT}	_	2.8	_	V		1
Triangular wave amplitude	ΔV_{CT}	_	1.6	_	V	$\Delta V_{CT} = V_{THCT} - V_{TLCT}$	1

Notes: 1. Reference value for design.

Electrical Characteristics (cont)

Error Amplifire Part / OVP Part

Item	Symbol	Min	Тур	Max	Unit	Test Condition	Note
Non-inverting input voltage	$V_{\sf FB}$	2.42	2.50	2.58	V	$V_{COMP} = 2.5 \text{ V}$	
Input bias current	I _{IB}	_	-0.2	-2.0	μΑ	V _{FB} = 5.0 V	
Open loop voltage gain	A _{VOL}	65	90	_	dB	$2.0 \text{ V} \le \text{V}_{\text{O}} \le 4.0 \text{ V}$	
Unity gain bank width	BW	0.7	1.0	_	MHz		
Power supply voltage rejection ratio	PSRR	60	70	_	dB	12 V ≤ V _{IN} ≤ 25 V	
Output sink current	I _{Osink EA}	3.0	9.0	_	mA	$V_{FB} = 2.7 \text{ V}, V_{COMP} = 1.1 \text{ V}$	
Output source current	l _{Osource EA}	-0.5	-0.8	_	mA	$V_{FB} = 2.3 \text{ V}, V_{COMP} = 5.0 \text{ V}$	
High level output voltage	V_{OHEA}	5.5	6.5	7.5	V	$V_{FB} = 2.3 \text{ V},$ $R_L = 15 \text{ k}\Omega(\text{GND})$	
Low level output voltage	V_{OLEA}	_	0.7	1.1	V	$V_{FB} = 2.7 \text{ V},$ $R_L = 15 \text{ k}\Omega(\text{Vref})$	
OVP latch threshold voltage	V_{OVP}	6.0	7.0	8.0	V	Increase FB terminal voltage	1
OVP (FB) terminal input current	I _{FB(OVP)}	_	30	50	μΑ	V _{FB} = 8.0 V	1
OVP latch reset V _{IN} voltage	V _{IN(OVP RES)}	6.0	7.0	8.0	V	Decreasing V _{IN} after OVP latched	1

Note: 1. These values are not prescribe to the HA17384SPS/SRP because OVP function is not included.

Electrical Characteristics (cont)

Current Sensing Part

Item	Symbol	Min	Тур	Max	Unit	Test Condition	Note
Voltage gain	A _{VCS}	2.85	3.00	3.15	V/V	$V_{FB} = 0 V$	1
Maximum sensing voltage	Vth _{cs}	0.9	1.0	1.1	V		
Power supply voltage rejection ratio	PSRR	_	70	_	dB	12 V ≤ V _{IN} ≤ 25 V	2
Input bias current	I _{BCS}	_	-2	-10	μΑ	$V_{CS} = 2 V$	
Current sensing response time	tpd	50	100	150	ns	Time from when V _{cs} becomes 2 V to when output becomes "L" (2 V)	3

Notes: 1. The gain this case is the ratio of error amplifier output change to the current-sensing threshold voltage change.

- 2. Reference value for design.
- 3. Current sensing response time tpd is definded a shown in the figure 1.

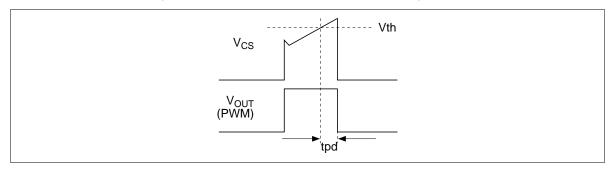


Figure 1 Definition of Current Sensing Response Time tpd

PWM Output Part

Item	Symbol	Min	Тур	Max	Unit	Test Condition	Note
Output low voltage 1	V_{OL1}	_	0.7	1.5	V	losink = 20 mA	
Output low voltage 2	V_{OL2}	_	1.5	2.2	V	losink = 200 mA	1
Output high voltage 1	V _{OH1}	13.0	13.5	_	V	losource = -20 mA	
Output high voltage 2	V_{OH2}	12.0	13.3	_	V	losource = -200 mA	1
Output low voltage at standby mode	V _{OL STB}	_	0.8	1.1	V	$V_{IN} = 5 V$, losink = 1 mA	
Rise time	t _r	_	80	150	ns	C _L = 1000 pF	
Fall time	t _f	_	70	130	ns	C _L = 1000 pF	
Maximum ON duty	Du max	94	96	100	%		
Minimum ON duty	Du min	_	_	0	%		

Notes: 1. Pulse application test

Electrical Characteristics (cont)

UVL Part

Item	Symbol	Min	Тур	Max	Unit	Test Condition	Note
Threshold voltage for	V_{THUVL}	14.5	16.0	17.5	V	Turn-ON voltage	1
high V _{IN} level		7.6	8.4	9.2	V	when V _{IN} is rising	2
Threshold voltage for	V _{TL UVL}	9.0	10.0	11.0	V	Minimum operating	1
low V _{IN} level		6.8	7.6	8.4	V	voltage after turn-ON	2
V _{IN} UVL hysteresis voltage	V _{HYS UVL}	5.0	6.0	7.0	V	$V_{HYSUVL} = V_{THUVL} - V_{TLUVL}$	1
		0.6	8.0	1.0	V	-	2
Vref UVL threshold voltage	V_{TVref}	4.3	4.7	Vref	V	Voltage is forced toVref terminal	

Notes: 1. For the HA17384S/H.

2. For the HA17385H.

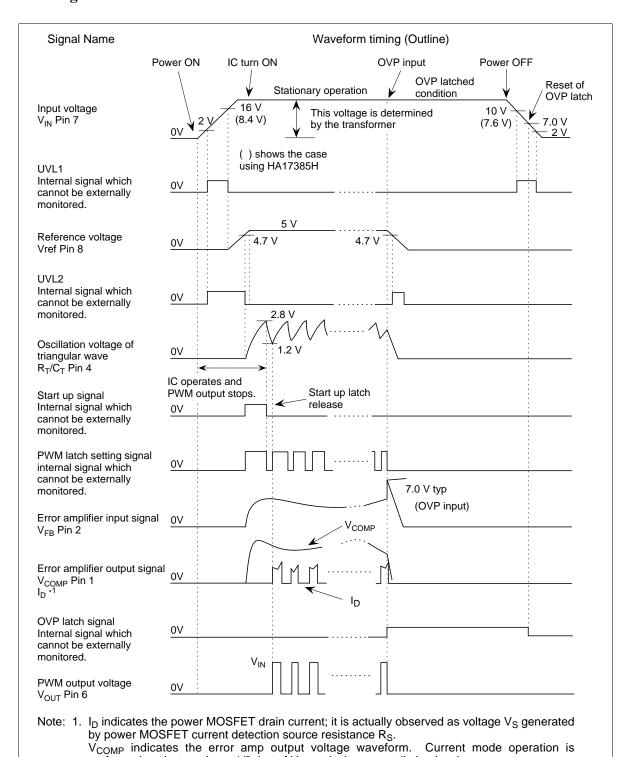
Total Characteristics

Item	Symbol	Min	Тур	Max	Unit	Test Condition	Note
Operating current	I _{IN}	7.0	10.0	13.0	mA	$C_L = 1000 \text{ pF}, V_{FB} = V_{CS} = 0 \text{ V}$	
Standby current	I _{STBY}	120	170	230	μΑ	Current at start up	
Current of latch	LATCH	200	270	340	μΑ	$V_{FB} = 0 \text{ V after } V_{FB} = V_{OVP}$	1, 2
Power supply zener voltage	V_{INZ}	31	34	37	V	I _{IN} + 2.5 mA	
Overheat protection starting temperature	Tj_{TSD}	_	160	_	°C		3, 4

Notes: 1. These values are not prescribe to the HA17384SPS/SRP because OVP function is not included.

- 2. $V_{IN} = 8.5 \text{ V}$ in case of the HA17384H.
- 2. These values are not prescribe to the HA17384SPS/SRP because TSD function is not included.
- 4. Reference value for design.

Timing Chart



performed so that a voltage 1/3 that of V_{COMP} is the current limiter level.

Operation (Description of Timing Chart)

From Power ON to Turn On

After the power is switched ON, the power supply terminal voltage (V_{IN}) of this IC rises by charging through bleeder resistor R_B . At this time, when the power voltage is in the range of 2 V to 16 V*\frac{1}{2}. The low-voltage, lock out UVL1 operates and accordingly the OUT voltage, that is, the gate voltage of the power MOSFET, is fixed at 1.3 V or a lower value, resulting in the power MOSFET remaining in the OFF state.

When the power supply voltage reaches 16 V, UVL1 of this IC is reset and the reference voltage (Vref) generating part turns ON. However, until Vref becomes 4.7 V, the low-voltage, lock out UVL2 operates to keep the OUT terminal voltage low. After Vref terminal voltage becomes 4.7 V or higher, OUT terminal outputs a PWM pulse.

Note: 1. The value is for the HA17384S/H.

The value is 8.4 V for the HA17385H.

Generation of Triangular Wave and PWM Pulse

After the output of the Vref, each blocks begins to operate. The triangular wave is generated on the R_T/C_T terminal. For PWM pulses, the triangular wave rise time is taken as the variable on-duty on-time. The triangular wave fall time is taken as the dead-band time. The initial rise of the triangular wave starts from 0 V, and to prevent a large on-duty at this time, the initial PWM pulse is masked and not output. PWM pulses are outputted after the second triangular wave. The above operation is enabled by the charge energy which is charged through the bleeder resistor R_B into the capacitor C_B of V_{IN} .

Stationary Operation

PWM pulses are outputted after the second wave of the triangular wave and stationary operation as the switching power supply starts.

By switching operation from ON/OFF to OFF/ON in the switching device (power MOSFET), the transformer converts the voltage. The power supply of IC V_{IN} is fed by the back-up winding of the transformer.

In the current mode of the IC, the current in the switcing device is always monitored by a source resistor R_{CS} . Then the current limiter level is varied according to the error voltage (COMP terminal voltage) for PWM control. One third of the error voltage level, which is divided by resistors "2R" and "R" in the IC, is used to sense the current ($R = 25 \text{ k}\Omega$).

Two diodes between the error output and the 2R-R circuit act only as a DC level shifter. Actually, these diodes are connected between the 2R-R circuit and GND, and, the current sensing comparator and GND, respectively. Therefore, these blocks operate 1.4 V higher than the GND level. Accordingly, the error of the current sensing level caused by the switching noise on the GND voltage level is eliminated. The zener diode of 1 V symbolically indicates that the maximum sensing voltage level of the CS terminal is 1 V.

Power OFF

At power OFF, the input voltage of the transformer gradually decreases and then V_{IN} of IC also decreases according to the input voltage. When V_{IN} becomes lower than 10 V*² or Vref becomes lower than 4.7 V, UVL1 (UVL2) operates again and the PWM pulse stops.

Note: 2. The value is for the HA17384S/H.

The value is 7.6 V for the HA17385H.

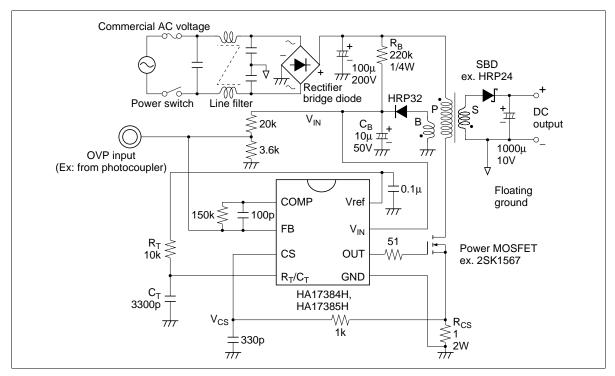


Figure 2 Mounting Circut Diagram for Operation Expression

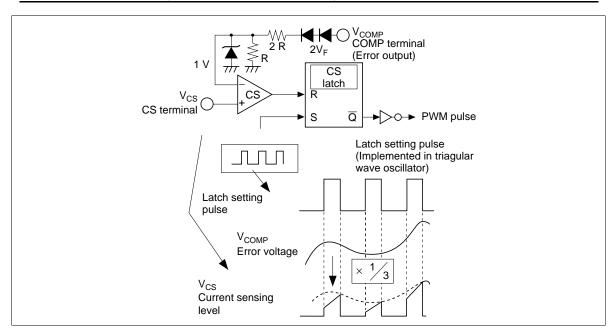


Figure 3 Operation Diagram of Current Sensing Part

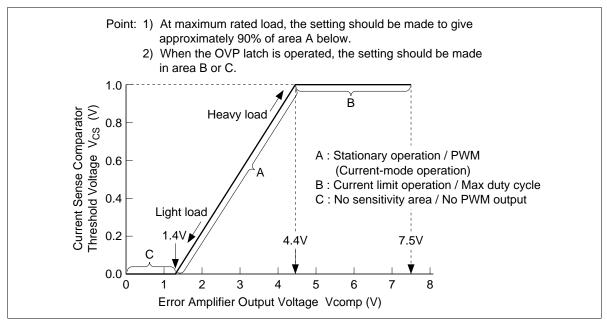


Figure 4 Current Sense Characteristics

Features and Theory of Current Mode Control

Features of Current Mode Control

- Switch element current detection is performed every cycle, giving a high feedback response speed.
- Operation with a constant transformer winding current gives a highly stable output voltage (with excellent line regulation characteristics, in particular).
- Suitable for flyback transformer use.
- External synchronous operation is easily achieved. (This feature, for example, is applicable to synchronization with a forizontal synchronizing signal of CRT monitor.)

Theory of Current Mode Control

In current mode control, a PWM pulse is generated not by comparing an error voltage with a triangular wave voltage in the voltage mode, but by changing the current limiter level in accordance with the error voltage (COMP terminal in this IC, that is,output of the error amplifier output) which is obtained by constantly monitoring the current of the switching device (power MOSFET) using source resistor R_{CS}.

One of the features of current mode control is that the current limited operates in all cycles of PWM as described by the above theory.

In voltage mode, only one feedback loop is made by an output voltage. In current mode, on the other hand, two loops are used. One is an output voltage loop and the other is a loop of the switching device current itself. The current of the switching device can be controlled switch high speed. In current mode control, the current in the transformer winding is kept constant, resulting in high stability. An important consequence is that the line regulation in terms of total characteristics is better than that in voltage mode.

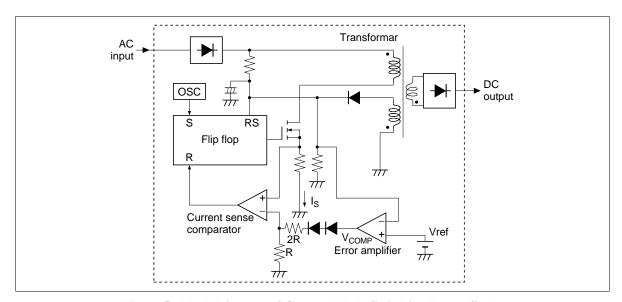
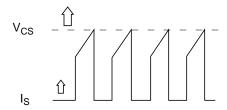
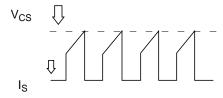


Figure 5 Block Diagram of Current Mode Switching Power Spply

A. Control in the case of heavy load



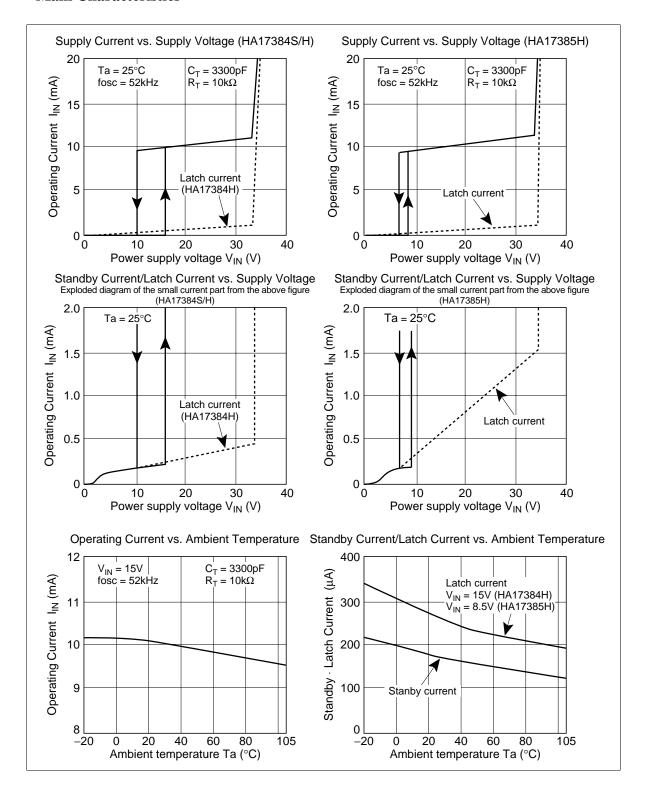
B. Control in the case of light load

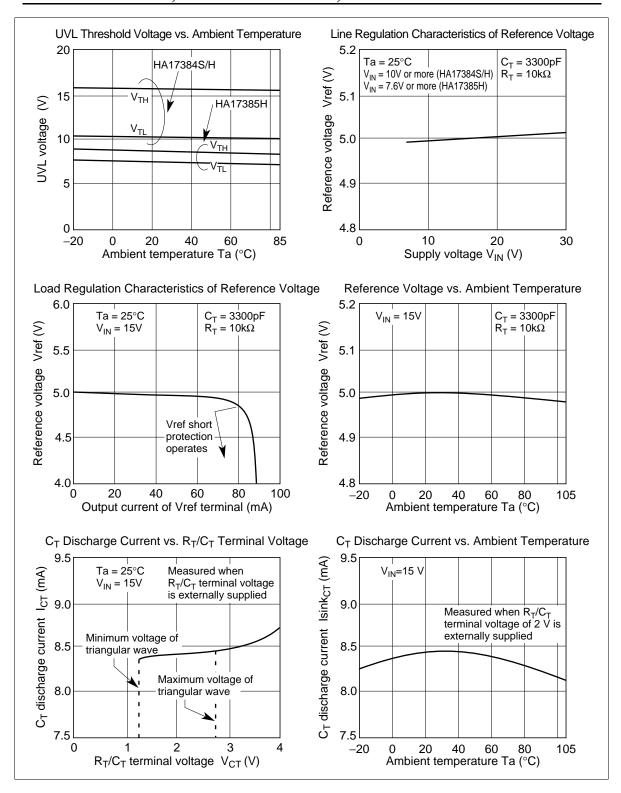


As the load becomes heavy and the DC output decreases, the current sensing level is raised as shown in A. above in order to increase the current in the switching device in each cycle. When the load decreases, inverse control is carried out as shown in B. above.

Figure 6 Primary Current Control of Transformer in Current Mode (Conceptual Diagram)

Main Characteristics





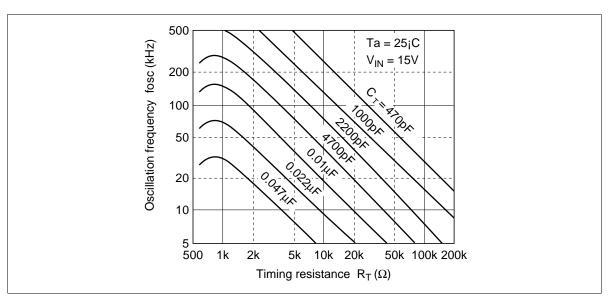


Figure 7 Oscillation Frequency vs. Timing Resistance

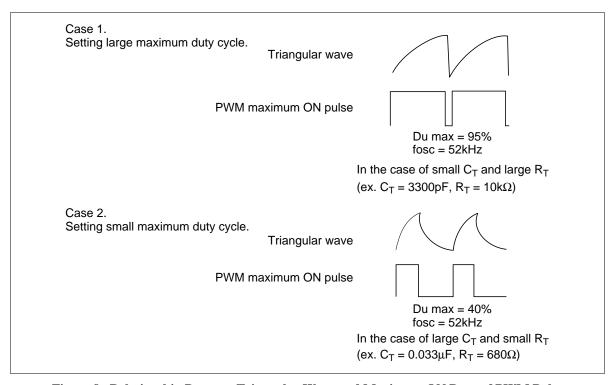


Figure 8 Relationship Between Triangular Wave and Maximum ON Duty of PWM Pulse

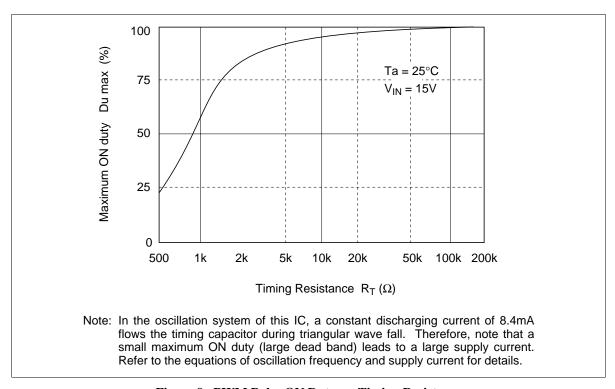
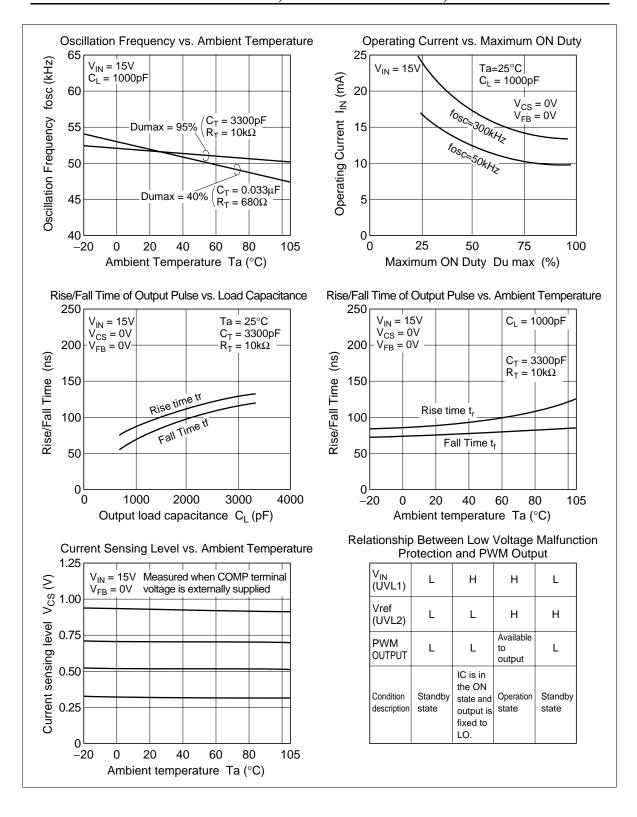


Figure 9 PWM Pulse ON Duty vs. Timing Resistance



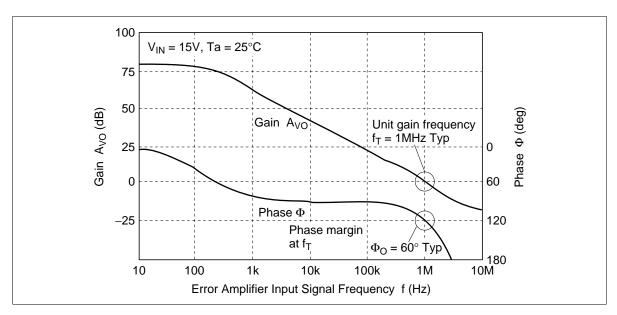


Figure 10 Open Loop Gain Characterisrics of Error Amplifier

- Calculation of operation parameters
 - 1. Maximum ON duty Du max (Refer to the right figure.)

Du max =
$$\frac{1}{1 + 1.78 \times \ln\left(1 + \frac{190\Omega}{R_T - 440\Omega}\right)}$$

2. Oscillation frequency fosc

$$\text{fosc} = \frac{1}{C_{\text{T}} \times R_{\text{T}} \times \left\{ 0.56 + \ln\left(1 + \frac{190\Omega}{R_{\text{T}} - 440\Omega}\right) \right\}}$$

From the above two equations, the following two equations are obtained.

3. Equalization to device R_T from Du max

$$R_{T} = \frac{190\Omega}{e^{0.56 (1/Du \text{ max} - 1)} - 1} + 440\Omega$$
(e = 2.71828.base of natural logarithm)

4. Equation to device C_T from fosc and R_T

$$C_T = 1.78 \times \frac{Du \text{ max}}{\text{fosc} \times R_T}$$

5. Operating current I_{IN}

$$I_{IN} = I_Q + Isink_{CT} \times (1 - Du max) + Ciss \times V_{IN} \times fosc$$

providing that I_Q = 8.4mA Typ (Supply current when oscillation in IC stops.) Ciss is the input gate capacitance of the power MOSFET which is connected and V_{IN} is the supply voltage of the IC.

Example 1: Calculation when $R_T = 10k\Omega$ and $C_T = 3300pF$

fosc = 52kHz, Du max = 95%, $I_{IN} = 9.7mA$

Example 2: Calculation for 50% of Du max and 200 kHz of fosc

$$R_T = 693\Omega$$
, $C_T = 6360 pF$, $I_{IN} = 12.5 mA$
However, Ciss = 1000 pF, $V_{IN} = 18 V$

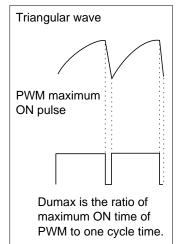
Note that the actual value may differ from the calculated one because of the internal delay in operation and input characteristics of the POWER MOS FET. Check the value when mounting.

Additionally a small Dumax leads to a large supply current, even if the frequency is not changed, and start up may become difficult. In such a case, the following measure is recommended.

- (1) For an AC/DC converter, a small bleeder resistance is required.
- (2) The large capacitance between Vref and GND is required.
- (3) Use a large Dumax with a triangular wave and raise the current limit of the switching device to around the maximum value (1.0V Typ).

The current limit is expressed as $ID_{max} = \frac{V_{THCS}}{R_{CS}}$





In the above case, Dumax = 95%

Application Circuit Example (1)

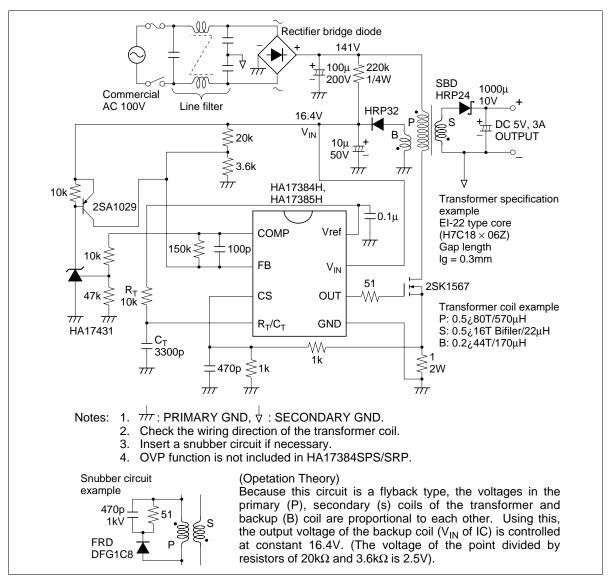


Figure 12 Primary Voltage Sensing Flyback Converter

Application Circuit Example (2)

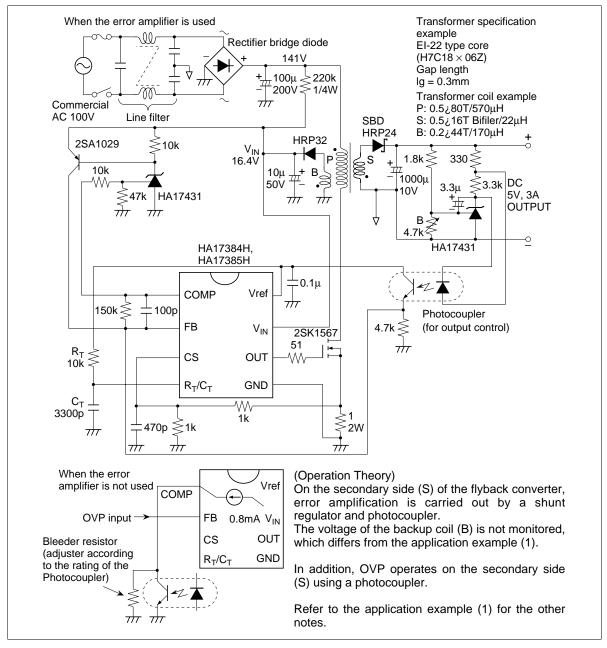


Figure 13 Secondary Voltage Sensing Flyback Converter

Application Examples for Fuller Exploitation of Power Supply Functions

A number of application examples are briefly described below.

1. Soft start

A soft start is a start method in which the PWM pulse width is gradually increased when the power supply is activated. This prevents the stress on the transformer and switch element caused by a rapid increase in the PWM pulse width, and also prevents overshoot when the secondary-side output voltage rises. The circuit diagram is shown in figure 14.

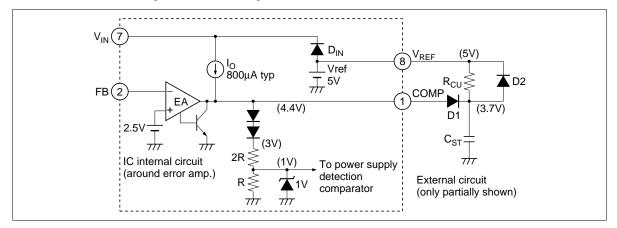


Figure 14 Circuit Diagram for Soft Start

Operation: In this circuit, error amp output source current $I_{\rm O}$ (800 μA typ.) gradually raises the switch element current detection level, using a voltage slope that charges soft start capacitance $C_{\rm ST}$. When the voltage at each node is at the value shown in parentheses in the figure, the soft start ends. The soft start time is thus given by the following formula:

$$T_{\text{ST}} = (3.7 \text{ V/800 } \mu\text{A}) \times C_{\text{ST}} \approx 4.62 \text{ C}_{\text{ST}} \text{ (ms)}$$

$$(C_{\text{ST}} \text{ unit: } \mu\text{F})$$

External parts other than C_{ST} operate as follows:

• Diode D1 : Current detection level shift and current reverse-flow prevention.

• Diode D2 : Together with diode D_{IN} in the IC, C_{ST} charge drawing when power supply falls.

• Resistance R_{CU} : For C_{ST} charge-up at end of soft start. (Use a high resistance of the order of several hundred $k\Omega$.)

Note: During a soft start, since PWM pulses are not output for a while after the IC starts operating, there is a lack of energy during this time, and intermittent mode may be entered. In this case, the capacitance between Vref and GND should be increased to around 4.7 μF to 10 μF.

2. OVP latch output overvoltage protection (the HA17384H and HA17385H only)

The OVP latch is incorporated in the error amp input pin (FB). If the FB pin is pulled up to 7.0 V typ. just once when the power supply enters any kind of error state, IC operation can be halted and held as it is (latched). To reset the latch, drop the IC's supply voltage to 7.0 V typ. or below momentarily. An OVP latch application example is shown in figure 15.

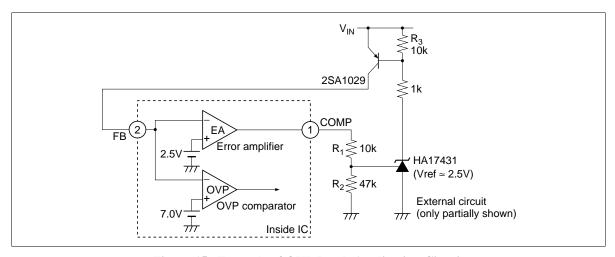


Figure 15 Example of OVP Latch Application Circuit

This circuit protects the system by causing latch operation in the event of an overload or load short. In the steady state, the error amp input/output pins operate at 2.5 V typ., but if the load becomes heavy the FB pin level drops and the COMP pin level rises. As shown in the figure, this is detected by the HA17431 shunt regulator, and the FB pin level is pulled up, operating the OVP latch.

The operation parameters are as follows:

COMP pin voltage detection level: Vth = $(R_1 + R_2) / R_2 \times 2.5 \text{ V}$

Notice for Use

1. OVP Latch Block

Case

When DC power is applied directly as the power supply of the HA17384H, HA17385H, without using the transformer backup coil. Also, when high-frequency noise is superimposed on the $V_{\rm IN}$ pin.

Problem

The IC may not be turn on in the case of a circuit in which $V_{\rm IN}$ rises quickly (10 V/100 μ s or faster), such as that shown in figure 16. Also, the OVP latch may operate even though the FB pin is normally at $V_{\rm OVP}$ or below after the IC is activated.

• Reason

Because of the IC circuit configuration, the timer latch block operates first.

• Remedy (counter measure)

Take remedial action such as configuring a time constant circuit (R_B , C_B) as shown in figure 17, to keep the V_{IN} rise speed below 10 V/100 μ s. Also, if there is marked high-frequency noise on the V_{IN} pin, a noise cancellation capacitor (C_N) with the best possible high-frequency characteristics (such as a ceramic capacitor) should be inserted between the V_{IN} pin and GND, and close to the V_{IN} pin.

When configuring an IC power supply with an activation resistance and backup winding, such as an AC/DC converter, the rise of V_{IN} will normally be around 1 V/100 μ s, and there is no risk of this problem occurring, but careful attention must be paid to high-frequency noise.

Also, this phenomenon is not occurring to the HA17384S, because OVP function is not built-in.

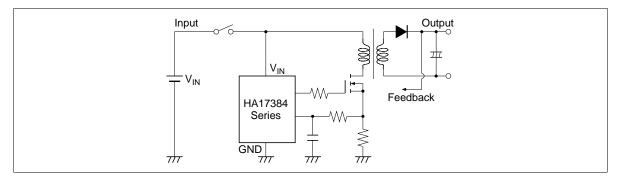


Figure 16 Example of Circuit with Fast V_{IN} Rise Time

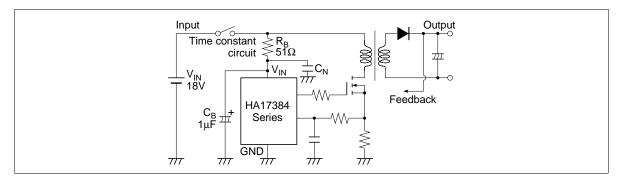


Figure 17 Sample Remedial Circuit

2. Externally Synchronized Operation

Case

When, with a power supply using the HA17384S/H or HA17385H, externally synchronized operation is performed by applying an external syncronous signal to the R_T/C_T pin (pin 4).

- Problem
 - Synchronized operation may not be possible if the amplitude of the external syncronous signal is too large.
- Reason

The R_T/C_T pin falls to a potential lower than the ground.

• Remedy (counter measure)

In this case, clamping is necessary using a diode with as small a V_F value as possible, such as a schottky barrier diode, as shown in figure 18.

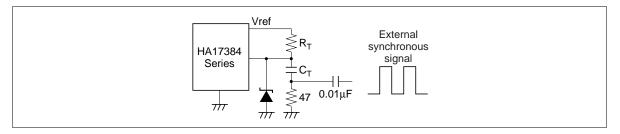
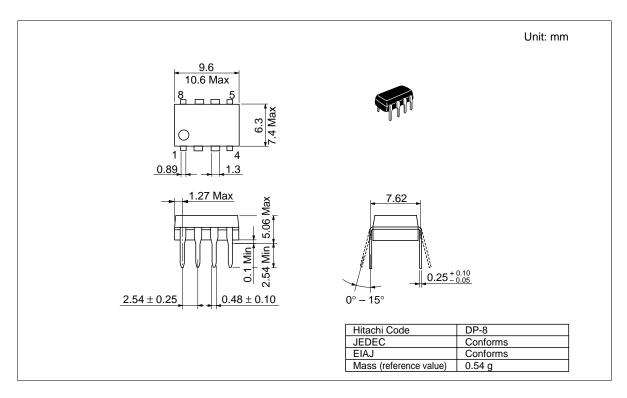
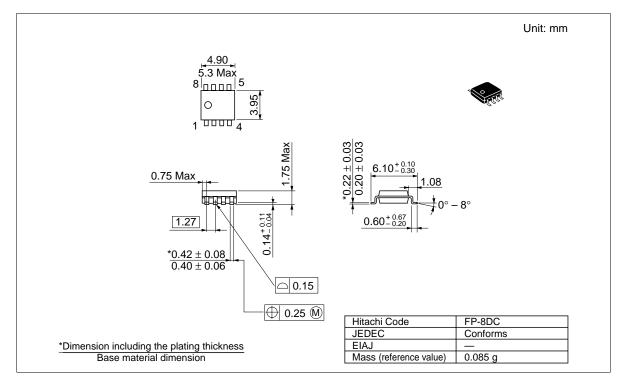


Figure 18 Sample Remedial Circuit

Package Dimensions





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